

ABSTRACT

A semiconductor memory device includes: a first stack structure and a second stack structure on a semiconductor substrate; a first vertical structure having a sidewall in contact with the first stack structure, the first vertical structure including a first memory layer and a first channel pattern; a second vertical structure having a sidewall in contact with the second stack structure, the second vertical structure including a second memory layer and a second channel pattern; a first bit line contact structure on the first vertical structure; and a first bit line overlapping with the first bit line contact structure. Each of the first stack structure and the second stack structure includes conductive layers stacked on the semiconductor substrate to be spaced apart from each other. The first bit line contact structure has a shape which is widened toward the first bit line.

FIG. 2B